

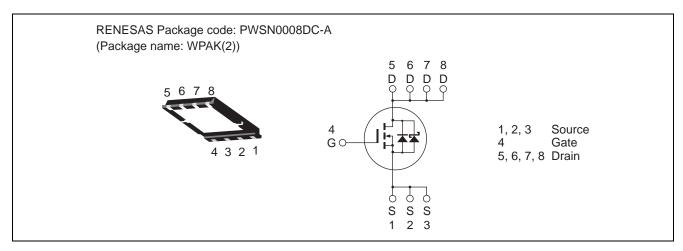
# RJK03E4DPA

# Silicon N Channel Power MOS FET with Schottky Barrier Diode Power Switching REJ03G1928-0210 Rev.2.10 May 20, 2010

#### **Features**

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance  $R_{DS(on)} = 2.8 \text{ m}\Omega \text{ typ. (at } V_{GS} = 8 \text{ V})$
- Pb-free
- Halogen-free

#### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	30	V
Gate to source voltage	V <sub>GSS</sub>	±12	V
Drain current	I <sub>D</sub>	45	Α
Drain peak current	I <sub>D(pulse)</sub> Note1	180	А
Body-drain diode reverse drain current	I <sub>DR</sub>	45	А
Avalanche current	I <sub>AP</sub> Note 2	17	Α
Avalanche energy	E <sub>AR</sub> Note 2	28.9	mJ
Channel dissipation	Pch Note3	40	W
Channel to case thermal impedance	θch-c Note3	3.13	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu s,\,duty\,\,cycle \leq$  1%

- 2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$
- 3.  $Tc = 25^{\circ}C$

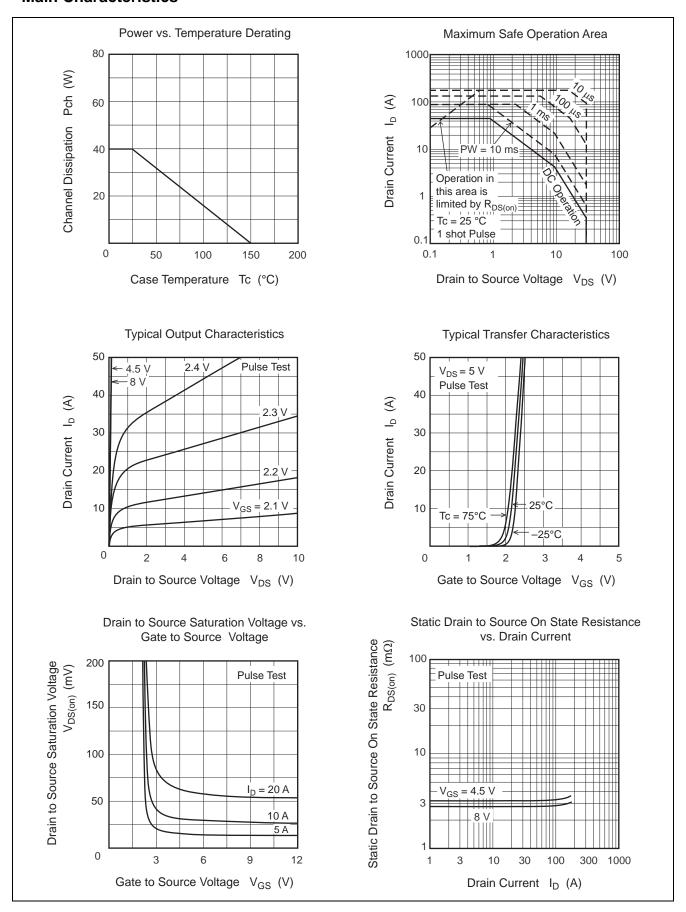
# **Electrical Characteristics**

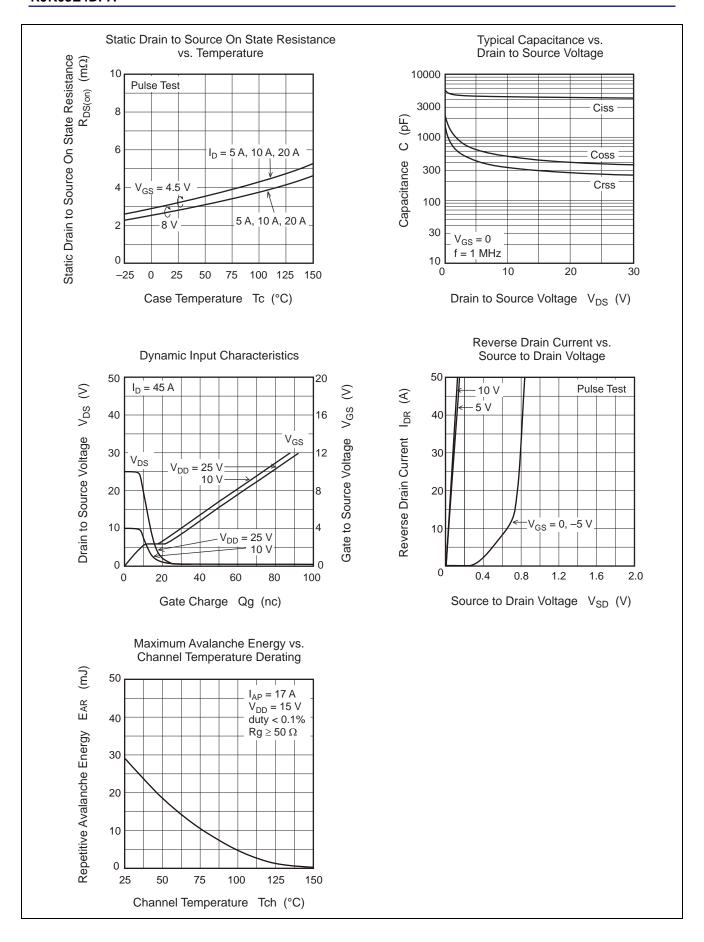
 $(Ta = 25^{\circ}C)$ 

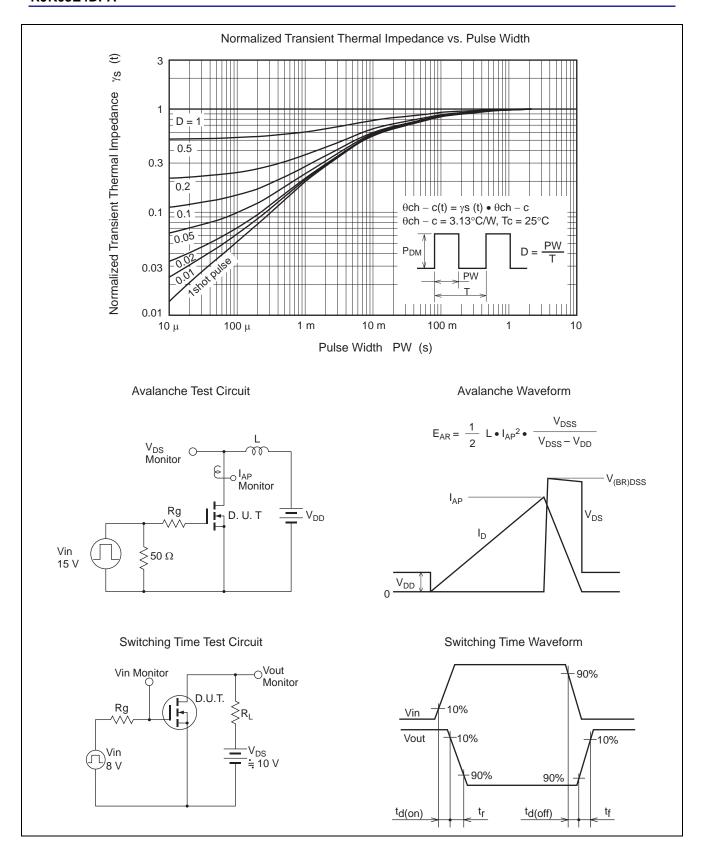
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	_	_	±0.1	μΑ	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	1	_	1	mA	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.2	_	2.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>	_	2.8	3.4	mΩ	$I_D = 22.5A, V_{GS} = 8.0 \text{ V}^{\text{Note4}}$
resistance	R <sub>DS(on)</sub>	_	3.2	4.0	mΩ	$I_D = 22.5A, V_{GS} = 4.5 V^{Note4}$
Forward transfer admittance	y <sub>fs</sub>	_	115	_	S	$I_D = 22.5A, V_{DS} = 5 V^{Note4}$
Input capacitance	Ciss	_	4300	6020	рF	$V_{DS} = 10 \text{ V}$
Output capacitance	Coss	_	500	_	рF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	330	_	рF	f = 1 MHz
Gate Resistance	Rg	_	1.7	3.4	Ω	
Total gate charge	Qg	_	33	_	nC	$V_{DD} = 10 \text{ V}$
Gate to source charge	Qgs	_	11	_	nC	$V_{GS} = 4.5 \text{ V}$
Gate to drain charge	Qgd	_	10	_	nC	I <sub>D</sub> = 45 A
Turn-on delay time	t <sub>d(on)</sub>	_	18	_	ns	$V_{GS} = 8 \text{ V}, I_D = 22.5 \text{ A}$
Rise time	t <sub>r</sub>	_	8	_	ns	$V_{DD} \cong 10 \text{ V}$
Turn-off delay time	t <sub>d(off)</sub>	_	66	_	ns	$R_L = 0.44\Omega$
Fall time	t <sub>f</sub>	_	17	_	ns	$Rg = 4.7 \Omega$
Body-drain diode forward voltage	$V_{DF}$		0.39	_	V	$I_F = 2 A, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery	t <sub>rr</sub>	_	29	_	ns	$I_F = 45 \text{ A}, V_{GS} = 0$
time						$di_F/dt = 100 A/ \mu s$

Notes: 4. Pulse test

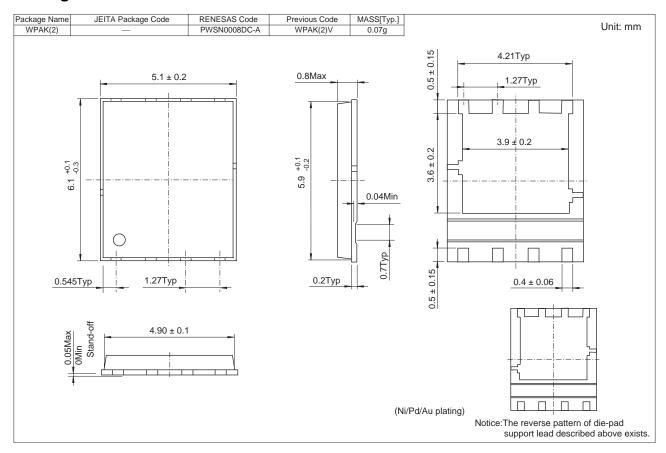
#### **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK03E4DPA-00-J53	3000 pcs	Taping

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